



### AC847BQ-AC847CQ-AC848BQ

#### **NPN SMALL SIGNAL TRANSISTOR IN SOT23**

### **Description**

The bipolar junction transistors (BJT) are designed to meet the stringent requirements of automotive applications.

### **Features**

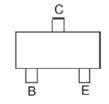
- Ideally Suited for Automatic Insertion
- Complementary PNP Types: AC857BQ AC857CQ AC858BQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

# **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)







Top View

Device Symbol

Top View Pin-Out

### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Quantity per Reel
AC847BQ-7	Automotive	2D1	7	3000
AC847CQ-7	Automotive	2C9	7	3000
AC848BQ-7	Automotive	2K9	7	3000
AC848BQ-13	Automotive	2K9	13	10,000

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



XXX = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Е	F	G	Н	ı	J	K	L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	AC847	V	50	V
Collector-base voltage	AC848	V <sub>CBO</sub>	30	] v
Callactor Emitter Voltage	AC847	V	45	V
Collector-Emitter Voltage	AC848	V <sub>CEO</sub>	30	\ \
Emitter-Base Voltage	AC847	V	6.0	V
Emilier-base vollage	AC848	V <sub>EBO</sub>	5.0	V
Continuous Collector Current	Ic	100	mA	
Peak Collector Current	I <sub>CM</sub>	200	mA	
Peak Emitter Current		I <sub>EM</sub>	200	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	310	mW	
Power Dissipation	(Note 7)	P <sub>D</sub>	350	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 6)	Б	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>OJA</sub>	357	C/VV	
Thermal Resistance, Junction to Leads (Note 8)		R <sub>ÐJL</sub>	350	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-65 to +150	°C	

# ESD Ratings (Note 9)

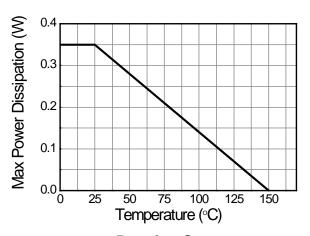
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

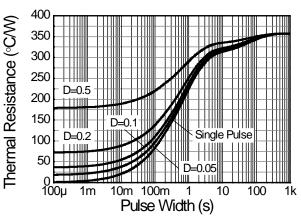
Notes:

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air 6. For a device mounted on minimum recommended pad layout 102 copper that is conditions whilst operating in a steady-state.
  7. Same as Note 6 except the device is mounted on 15mm x 15mm 1oz copper.
  8. Thermal resistance from junction to solder-point (at the end of the leads).
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



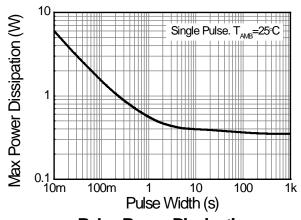
## **Thermal Characteristics and Derating Information**





# **Derating Curve**

Transient Thermal Impedance



**Pulse Power Dissipation** 



### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage		AC847	D\/	50	_	-	V	$I_C = 10\mu A$	
AC848		AC848	BV <sub>CBO</sub>	30	_	1	_	_	
Collector-Emitter Breakdown Voltage (Note 10)		AC847	D\/	45	_	-	V	$I_C = 10mA$	
Collector-Enlitter Breakdown Voltage (Note	; 10)	AC848	BV <sub>CEO</sub>	30	_	1	_	—	
Emitter-Base Breakdown Voltage		AC847	BV <sub>EBO</sub>	6	_	1	V	$I_E = 1\mu A$	
Emitter base breakdown voltage		AC848	PAERO	5	_		_	_	
Collector Cutoff Current			1			15	nA	$V_{CB} = 30V$	
Collector Cutoff Current			I <sub>CBO</sub>			5	μΑ	$V_{CB} = 30V, T_J = +150^{\circ}C$	
Collector Emitter Cutoff Current			ICES	_	_	15	nA	V <sub>CE</sub> = 50V	
Emitter Base Cutoff Current			I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 5V	
Small Signal Current Gain (Note 10)	AC84	7BQ/AC848BQ	h.		330				
Small Signal Current Gain (Note 10)		AC847CQ	h <sub>fe</sub>		600		_		
Input Impedance (Note 10)		7BQ/AC848BQ	h <sub>ie</sub>		4.5		kΩ		
input impedance (Note 10)		AC847CQ	rile		8.7			$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$	
Output Admittance (Note 10)		7BQ/AC848BQ	h <sub>oe</sub>	_	30	_	μs	f=1.0kHz	
		AC847CQ	1.06		60			-	
Reverse Voltage Transfer Ratio (Note 10)		7BQ/AC848BQ	h <sub>re</sub>	_	2x10 <sup>-4</sup>	_	_		
Trovoros voltago manoror mano (rvoto 10)		AC847CQ	THE		3x10 <sup>-4</sup>				
DC Current Gain (Note 10)		7BQ/AC848BQ	h <sub>FE</sub>	200	290	450	_	$I_{C} = 2.0 \text{mA}, V_{CE} = 5 \text{V}$	
De danem dam (Note 16)		AC847CQ		420	520	800		,	
Collector-Emitter Saturation Voltage (Note	10)		V <sub>CE(SAT)</sub>	_	90	250	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	
Concotor Emilior Cataration Voltage (Note	10)		V CE(SAT)		200	600		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Turn-On Voltage (Note 10)			V <sub>BE(ON)</sub>	580	660	700	mV	$I_C = 2mA$ , $V_{CE} = 5V$	
Base Emilier rum on voltage (Note 10)			v BE(ON)		_	770	111.0	$I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$	
Base-Emitter Saturation Voltage (Note 10)			.,		700		mV	$I_C = 10mA, I_B = 0.5mA$	
Base-Emilier Saturation Voltage (Note 10)			V <sub>BE(SAT)</sub>	AT) —	900	_	IIIV	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$	
Output Capacitance			C <sub>OBO</sub>		3		pF	V <sub>CB</sub> = 10V, f = 1.0MHz	
Transition Frequency			f⊤	100	300	_	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA, f = 100MHz	
Noise Figure			NF	_	2	10	dB	$V_{CE}$ =5V, $I_{C}$ =200 $\mu$ A $R_{S}$ =2k $\Omega$ , f=1kHz $\Delta$ f=200Hz	

Note:

10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

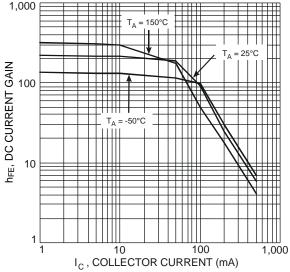


Figure 1 Typical DC Current Gain vs. Collector Current

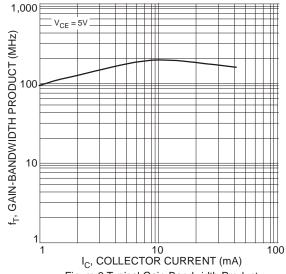


Figure 3 Typical Gain-Bandwidth Product vs. Collector Current

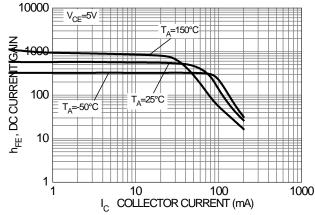


Figure 5 Typical DC Current Gain vs. Collector Current (Band C Group Gain)

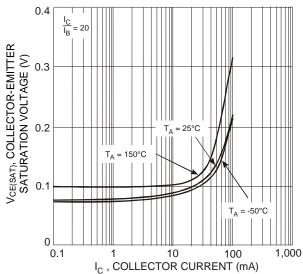


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

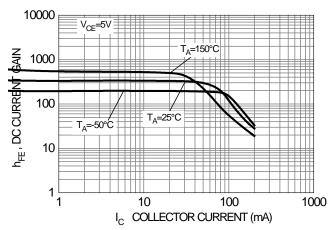
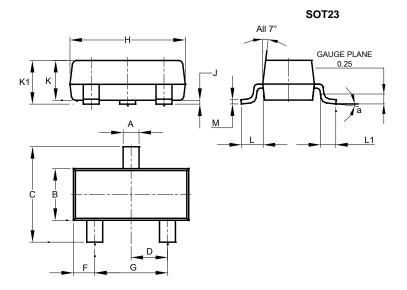


Figure 4 Typical DC Current Gain vs. Collector Current (Band B Group Gain)



## **Package Outline Dimensions**

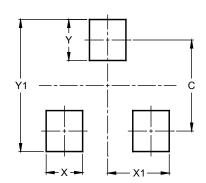
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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